TOSHIBA MOS MEMORY PRODUCTS

TC531000CP-12, TC531000CP TC531000CF-12, TC531000CF

DESCRIPTION

The TC531000CP/CF is a 1,048,576 bits read only memory organized as 131,072 words by 8 bits with a low bit cost, thus being suitable for use in program memory of microprocessor, especially character generator. The TC531000CP/CF using CMOS technology is most suitable for low power applications where battery operation are required. The TC531000CP/CF has one chip enable input $\overline{\text{CE}}/\text{CE}$, programmable for device selection.

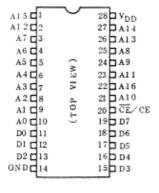
FEATURES

TC531000CP/CF		120ns Version	150ns Version
Access Time	(max.)	120ns	150ns
Power Dissipation Operation Current	(max.)	40mA	35mA
Power Dissipation Standby Current	(max.)	20μΑ	20μA

- · Single 5V Power Supply
- · All Inputs and Outputs: TTL Compatible
- · Three State Outputs
- · Fully Static Operation
- · Programmable Chip Enable
- Package

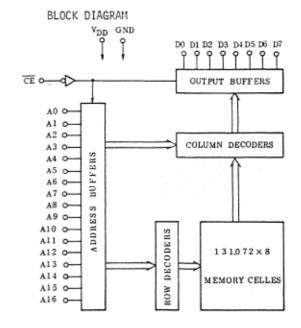
Plastic DIP: TC531000CP Plastic FP: TC531000CF

PIN CONNECTION



PIN NAMES

A0 ~ A16	Address Inputs
D0 ∿ D7	Data Outputs
CE/CE	Chip Enable Input
VDD	Power Supply
GND	Ground



MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT	
V _{DD}	Power Supply Voltage	-0.5 ∿.7.0		
V _{IN} Input Voltage		-0.5 ∿ V _{DD}	V	
V _{OUT}	Output Voltage	o ∿ V _{DD}		
PD	Power Dissipation	1.0/0.6 *	W	
TSTG	Storage Temperature	-55 ∿ 150	°c	
TOPR	Operating Temperature	-40 ∿ 70		
T _{SOLDER}	Soldering Temperature • Time	260 · 10	°C•sec	

Note: * Plastic FP

DC OPERATING CONDITIONS (Ta=-40 ~ 70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
v_{DD}	Power Supply Voltage	4.5	5.0	.5.5	
VIH	Input High Voltage	2.2	-	V _{DD} +0.3	V
VIL	Input Low Voltage	-0.3	-	0.8	

DC and OPERATING CHARACTERISTICS (Ta=-40 ~ 70°C, VDD=5V±10%)

SYMBOL	PARAMETER	CONDITIONS		MIN.	MAX.	UNIT
IIL	Input Leakage Current	$V_{\rm IN}=0 \sim V_{\rm DD}$		-	±1.0	
ILO	Output Leakage Current	CE=VIH, VOUT=0 ~ VI	CE=VIH, VOUT=O ~ VDD		±5.0	μА
IOH	Output High Current	V _{OH} =2.4V		-1.0	-	
IOL	Output Low Current	V _{OL} =0.4V		3.2	-	mA
IDDS1	Standby Current	CE=0.8V (CE=2.2V)		T -	2	
IDDS2	Standby Current	CE=0.2V (CE=VDD-0.2V)		-	20	μA
Tanas		V _{IN} =V _{IH} /V _{IL}	t _{cycle} =120ns	-	50	,
I _{DD01}	0	I _{OUT} =0mA	t _{cycle} =150ns	-	45	mA
Innaa	Operating Current	V _{IN} =V _{DD} -0.2V/0.2V		-	40	aux
I _{DD} 02	-DD02	I _{OUT} =OmA t _{cycle} =150ns		-	35	

CAPACITANCE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
CIN	Input Capacitance	f=1MHz, Ta=25°C	-	10	рF
COUT	Output Capacitance	f=1MHz, Ta=25°C	-	10	pr

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS (VDD=5V±10%, Ta=-40 ~ 70°C)

SYMBOL	PARAMETER	120ns Version		150ns Version		UNIT
		MIN.	MAX.	MIN.	MAX.	0
t _{cycle}	Cycle Time	120	-	150	-	
tACC	Access Time	-	120	-	150]
t _{CE}	Chip Enable Access Time	-	120	-	150	ns
tCED	Output Disable Time	-	50	-	50	1
tOH	Output Hold Time	5	-	5	-	1

AC TEST CONDITION

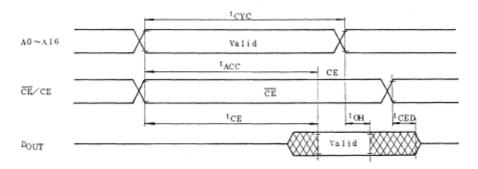
• Output Load. : 100pF + 1TTL • Input Levels : 0.6V, 2.4V

· Timing Measurement Reference Levels

Input: 0.8V, 2.2V Output: 0.8V, 2.0V

• Input Rise and Fall Time : 5ns

TIMING WAVEFORMS



OPERATING MODE

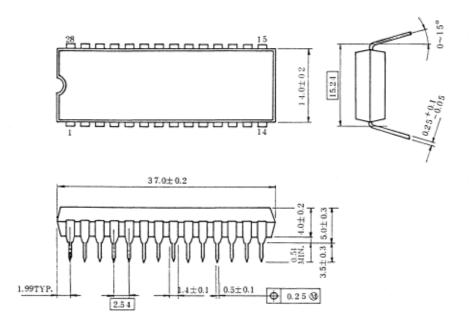
MODE	CE(CE)	AO ∿ 16	Outputs	Power
Read	L(H)	Valid	Data Out	Operating
Standby	H(L)	×	High-Z	Standby

H: VIH, L: VIL, *: VIH or VIL

OUTLINE DRAWINGS

Plastic DIP (DIP28-P-600)

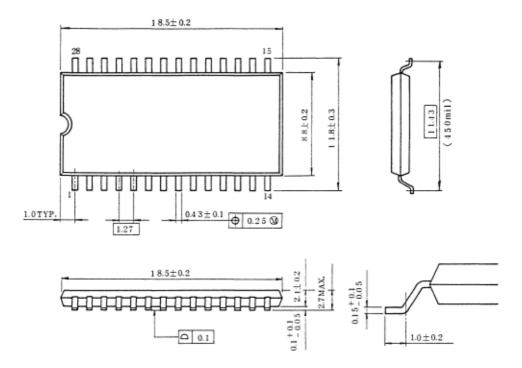
Unit in mm



Note: Package width and length do not include mold protrusion, allowable mold protrusion is 0.15mm.

Plastic FP (SOP28-P-450)

unit in mm



Note: Package width and length do not include mold protrusion, allowable mold protrusion is 0.15mm.